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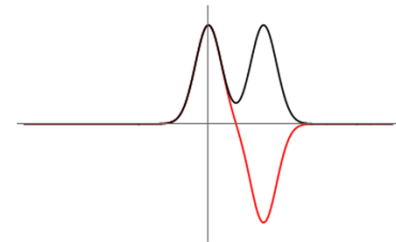
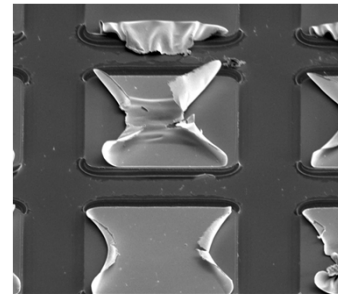
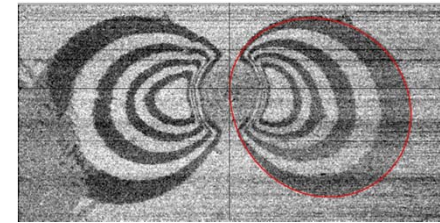
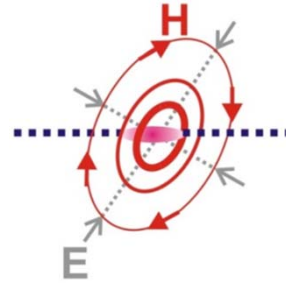
# Material Studies with Compressed Electron & Positron Beams

Ioan Tudosa



# Outline

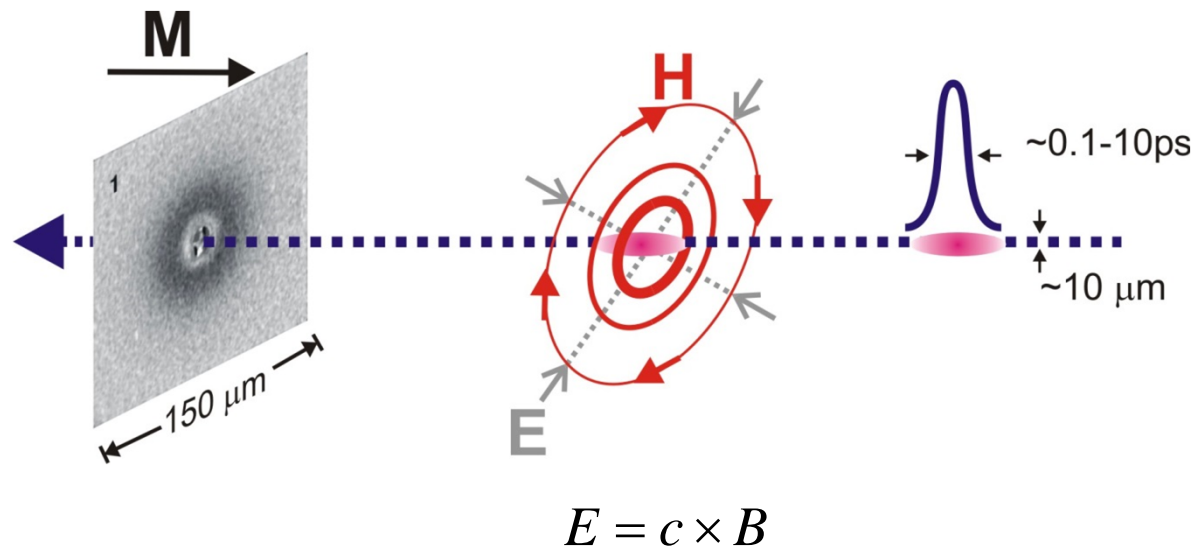
- EM field of Facet
- Magnetic probe of spin memory
- Mechanical probe of resistive memory
- Two bunch probe use



# Accelerated Bunch

- Magnetic and electric fields  
(plane wave, radial polarized)
- Intense and short pulses  
(peak:  $E \sim 1 \text{ V/\AA}$ ,  $B \sim 30 \text{ T}$ )

$$H \sim \frac{I}{r} \sim \frac{Q/\tau}{r}$$



# Electron/Positron Bunch Parameters

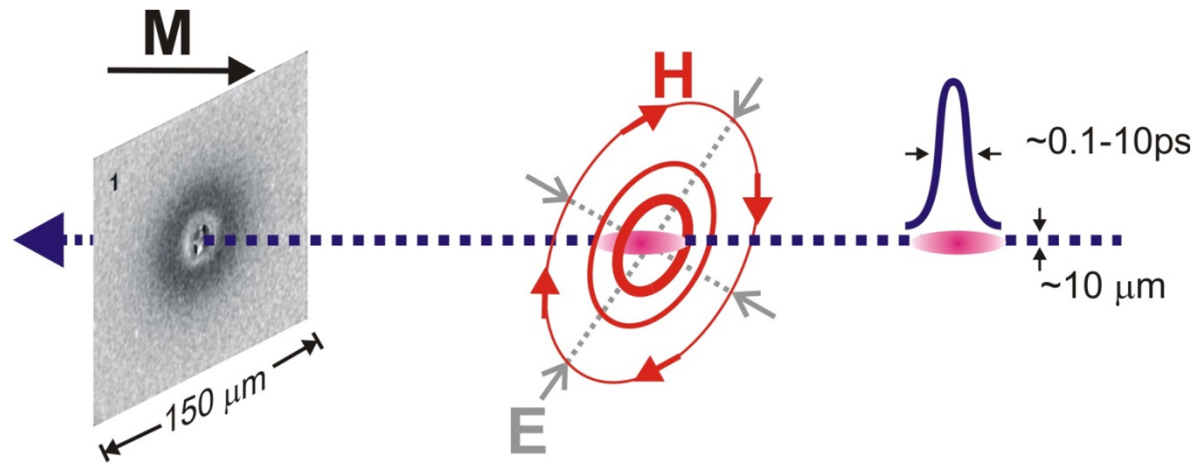
Energy	10 GeV
Charge	2 nC / 1 nC
Bunch Length	20 $\mu\text{m}$
Spot Size	20 $\mu\text{m}$
Peak Current	10 kA / 5 kA
Bunch Spacing	0-500 $\mu\text{m}$



# Probing magnetic spin systems

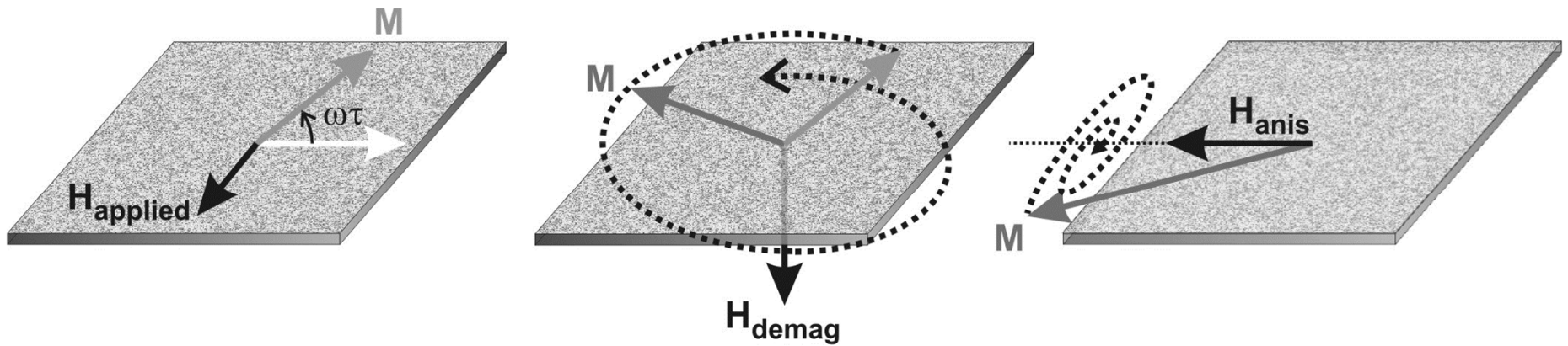
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- Pass bunch through magnetic thin films
- Image pattern afterwards



# Precessional Magnetization Reversal

## 3 Step Process



Field Pulse Kick

$$\theta = \omega\tau$$

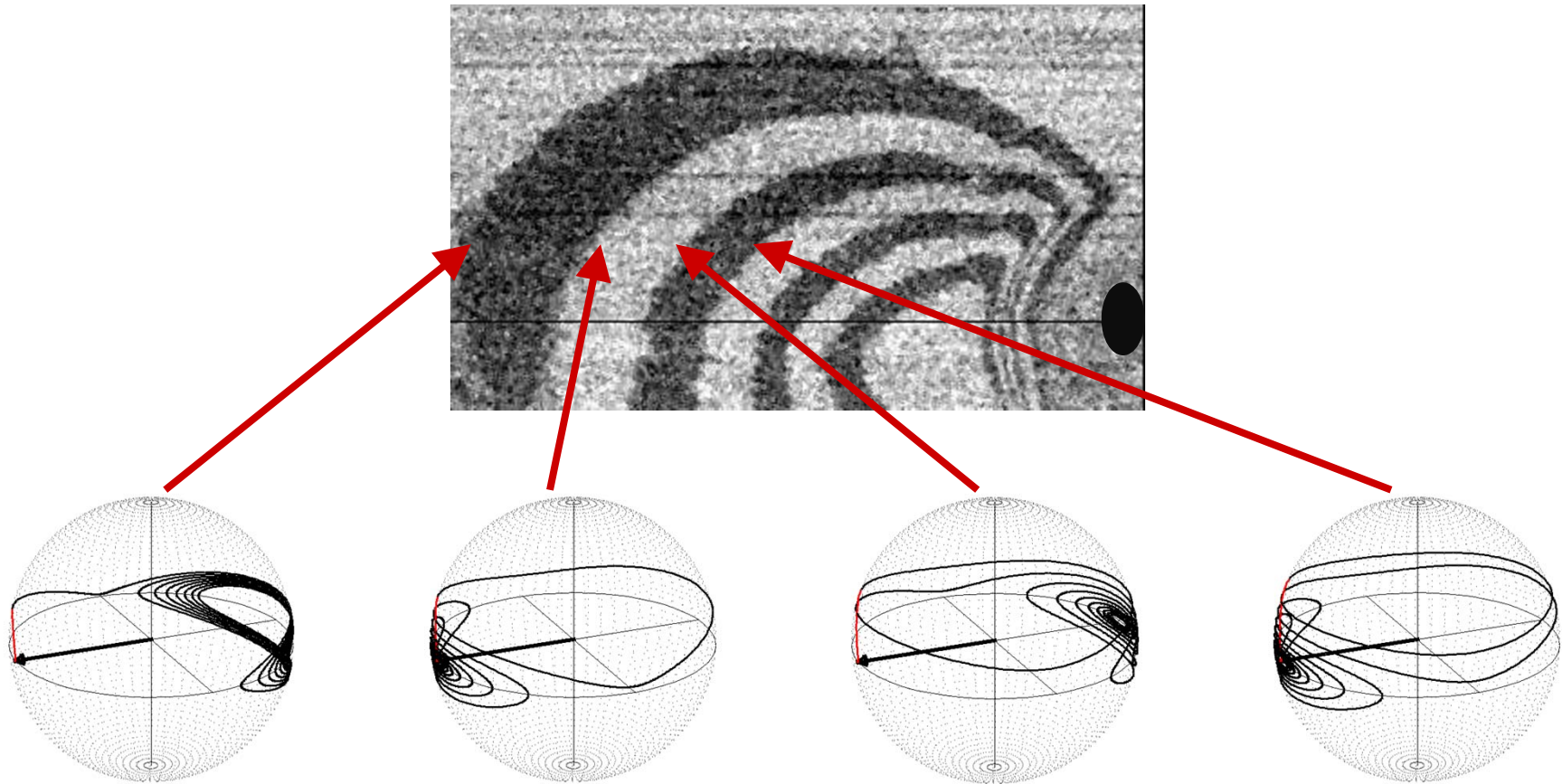
Rotations Around  $H_{\text{demag}}$

$$\varphi = \pi, 2\pi, 3\pi \dots$$

Final Alignment

# Dynamics of Magnetization

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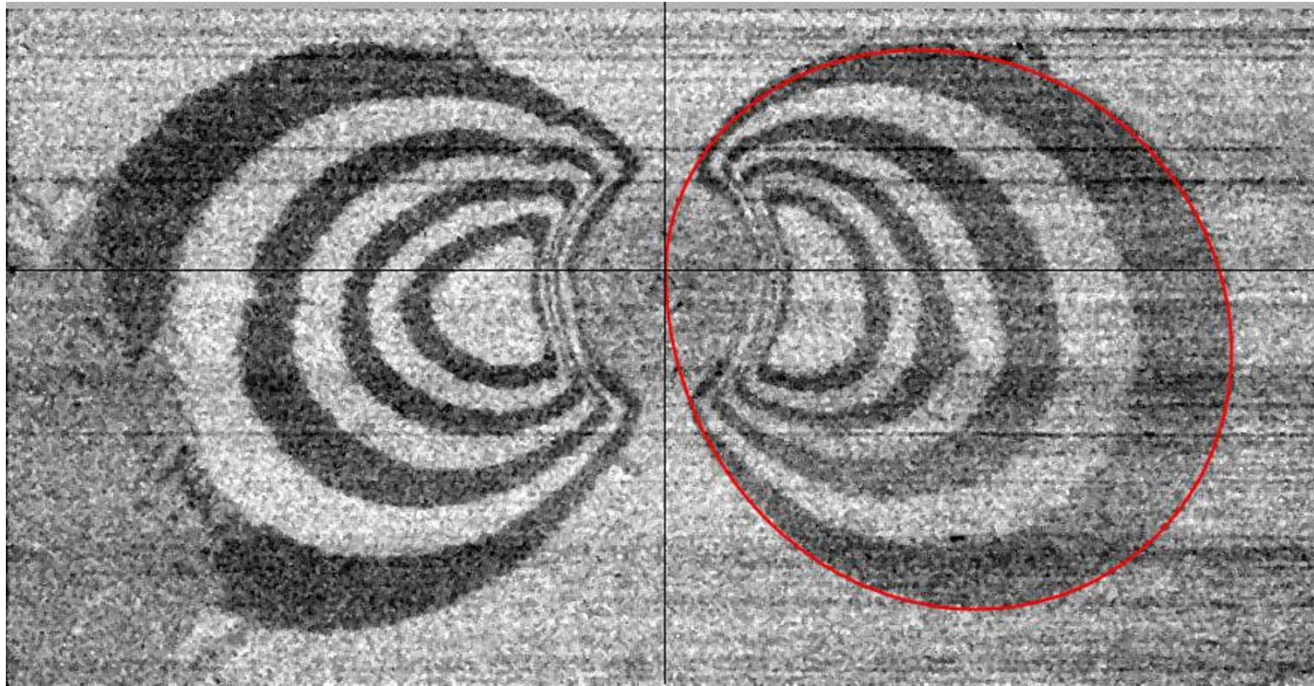


Damping dissipates the energy pumped into the system → ring location

# Extra Torque

- Distortion from circle  $\rightarrow$  extra torque
- Ratio of extra / magnetic torque:

$$\kappa = \frac{T_E}{T_H} = 0.15$$



Sample:  
4nm Ag / 60 ML Fe / W(110)

In polar coordinates

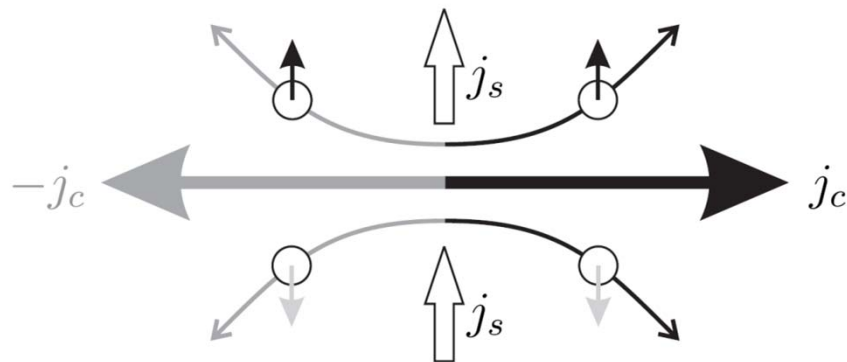
$$\frac{\cos \theta - \kappa \cdot \sin 2\theta}{r} = \text{const}$$



# Spin-Orbit Coupling and Spin Accumulation

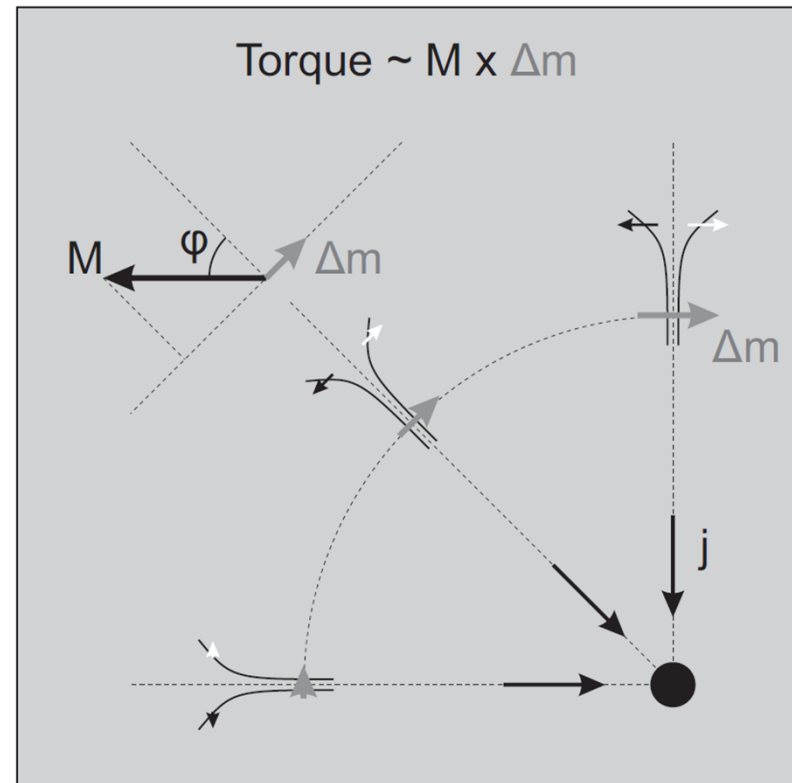
## Anomalous Hall Effect

Spin-orbit coupling bends trajectory of  $e^-$  in eddy currents  $j_c \rightarrow$  Spin current  $j_s$



A second  $e^+$  bunch:

- Subtract from magnetic torque
- Adds to this extra torque

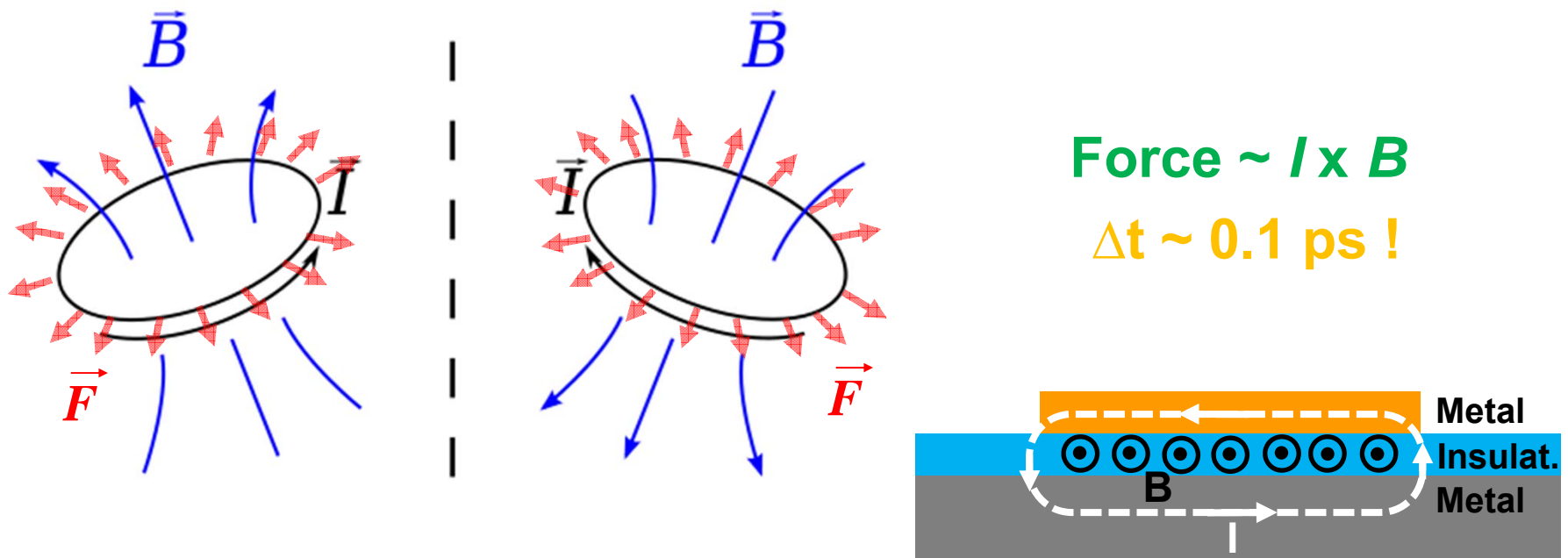


Spin current  $\rightarrow$  Spin accumulation  $\rightarrow$  Torque  $\Delta m$



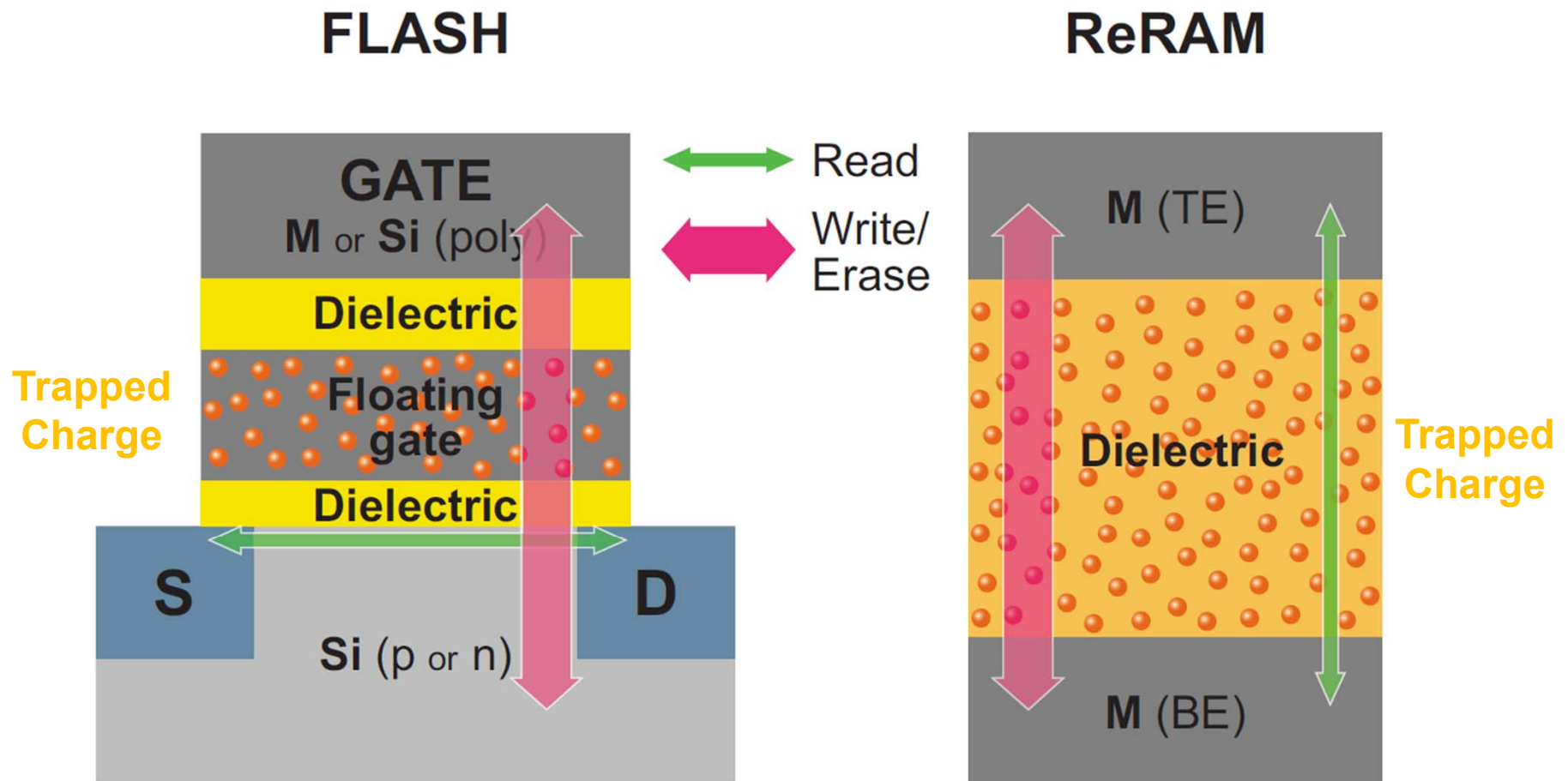
# FACET Provides A Lorentz Force Switch

- Tensile self-force on a coil w current
- Transient  $B \longrightarrow$  transient force
- EM coupling to MIM structure



# Nonvolatile Memory

Voltage-Time dilemma due to **read-write** paths



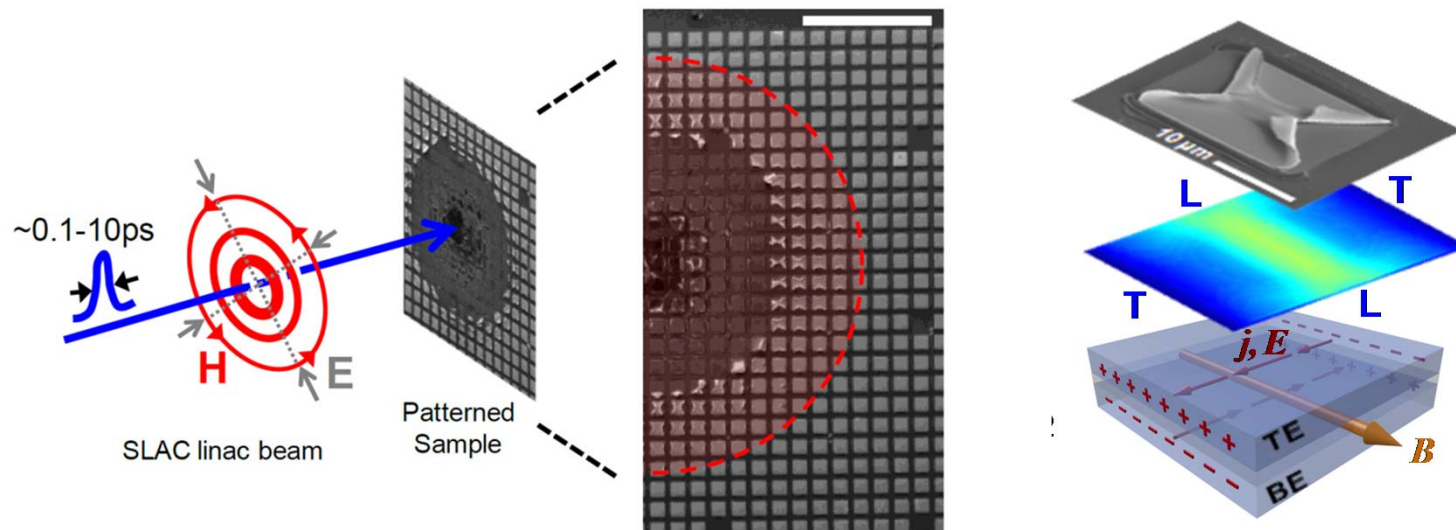
# Open Questions

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- Temporal limit of switching?
- **Role of atom lattice in trapping?**
- **Fast electro-mechanical probe!**



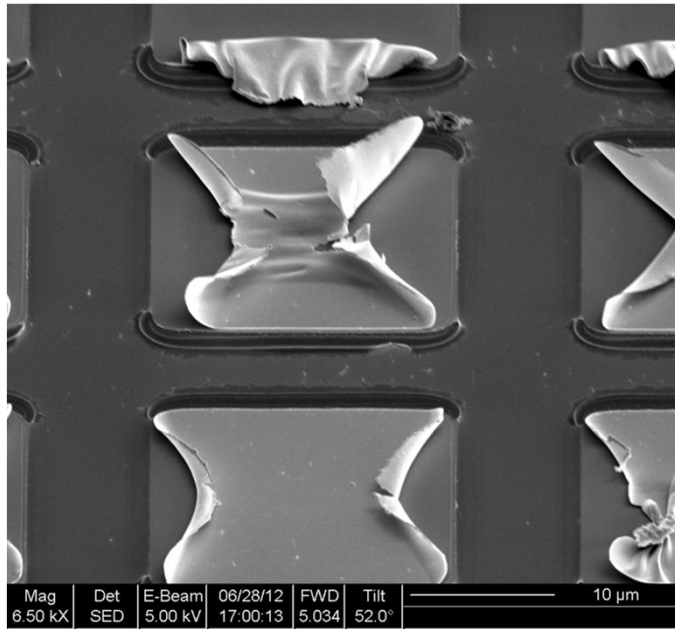
# Principle of the experiments



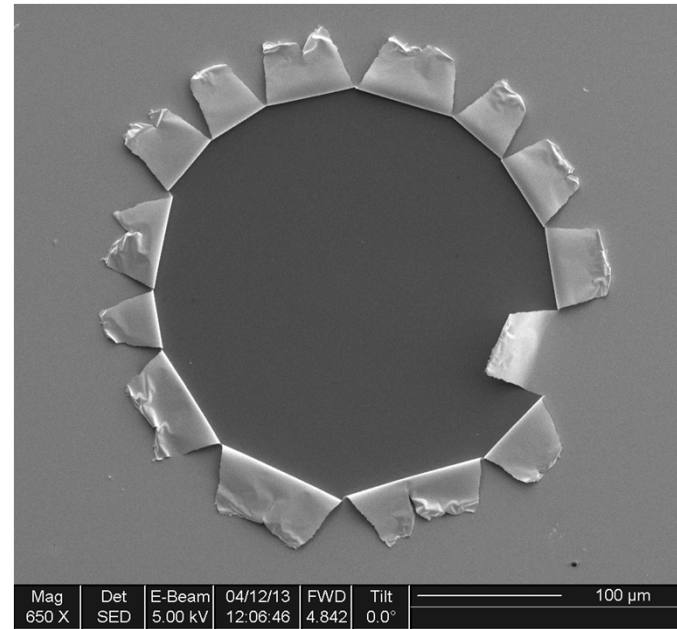
Array of devices exposed to e-beam  
Probe and image afterwards

# Top Electrode Damage

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**Rectangular Pad**

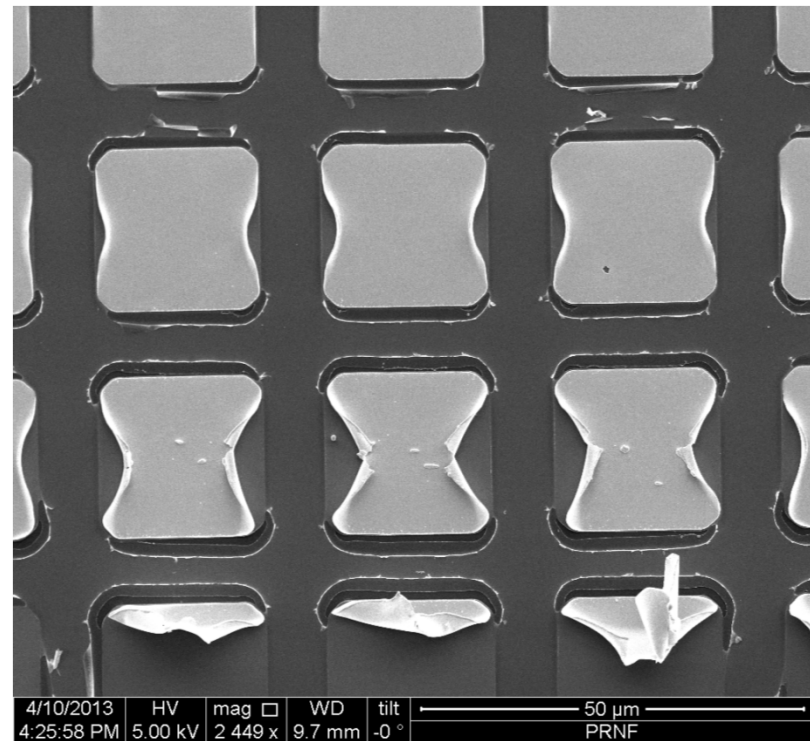
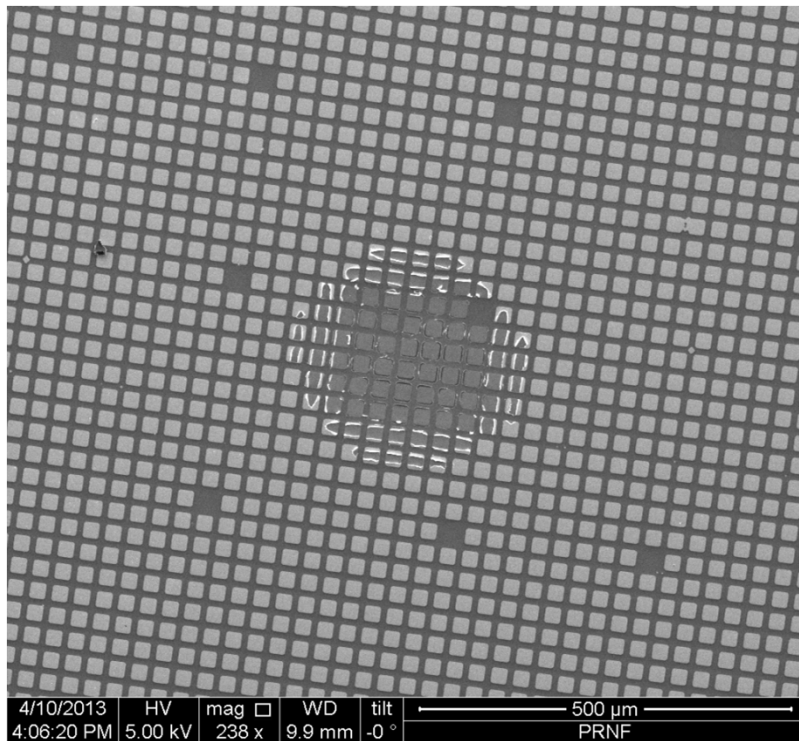


**Continuous Film**



# Top Electrode Damage

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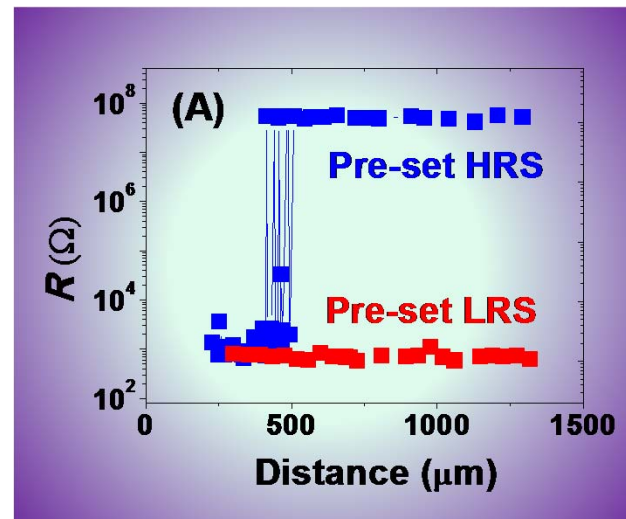
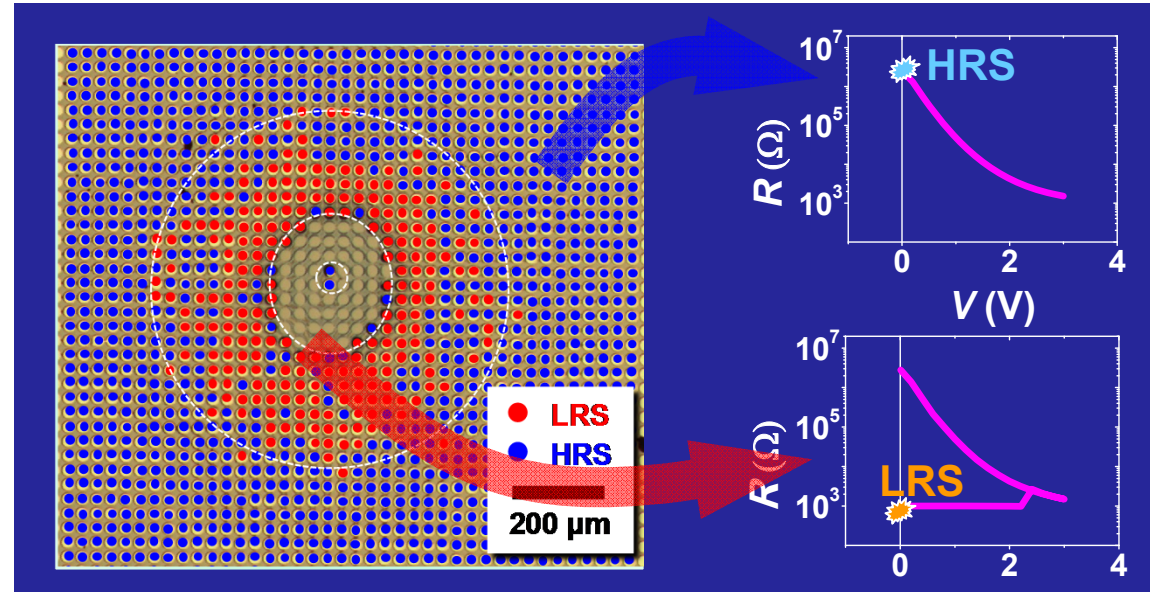


# Switching Results

Only High-R state is switched

Mechanical effect points to relaxation of atomic bonds

Solve voltage-time dilemma by electron-lattice interaction



All Cells  
Preset to  
HRS

# Opportunities at FACET

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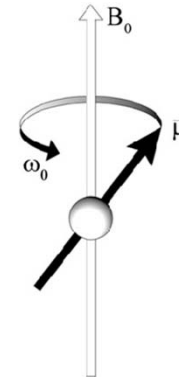
- *Strong* 100 fs field impulse
- Well coupled to 10s  $\mu\text{m}$  MIM device
- Magnetic-mechanical-electric probe
- Time scale  $\sim$  Atomic motion

# Scaling of Effects

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- Spin precession angle

$$\theta = \omega\tau \sim B\tau \sim \frac{I}{r}\tau \sim \frac{Q}{r}$$



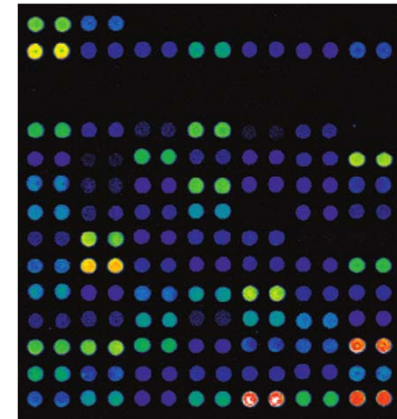
- Mechanical Impulse

$$\Delta p = F\tau \sim B^2\tau \sim \frac{I^2}{r^2}\tau \sim \frac{QI}{r^2}$$

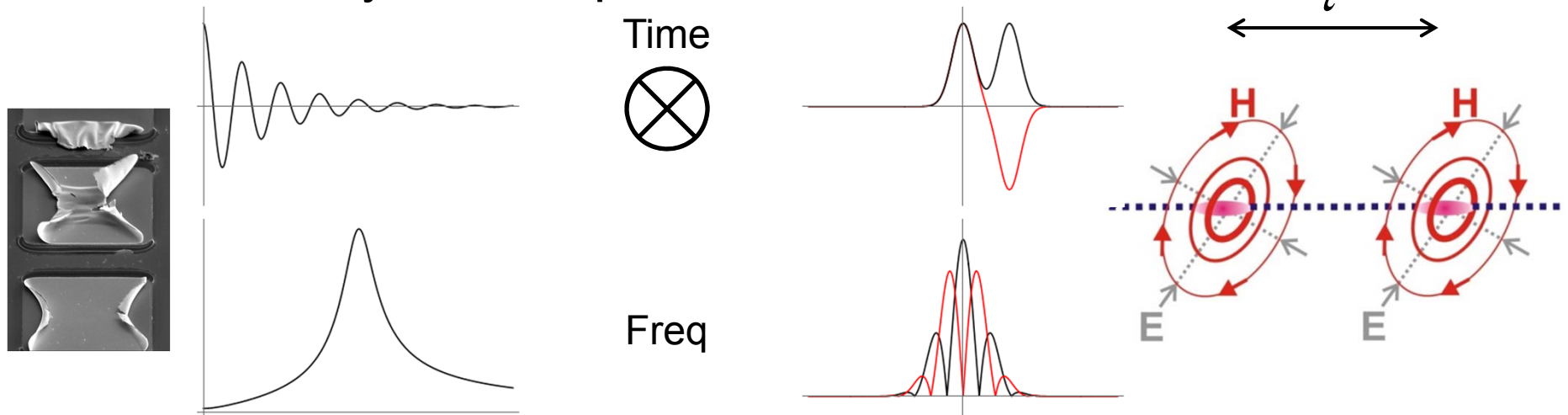
- Maximize charge  $Q$  and current  $I$
- Minimize bunch spot size  $\sigma_r$

# Experiments with two bunches

- Method: “*double pump - probe later*”
- For systems with memory
- Take many shots, image later  
(like in DNA microarray)



- Extract system response from convolution



# End

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